

# isc N-Channel MOSFET Transistor

# STB12NK80Z

#### **DESCRIPTION**

- Drain Current : I<sub>D</sub>= 10.5A@ T<sub>C</sub>=25 °C
- Drain Source Voltage
- : V<sub>DSS</sub>= 800V(Min)
- · Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 0.75 \Omega (Max) @ V_{GS} = 10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



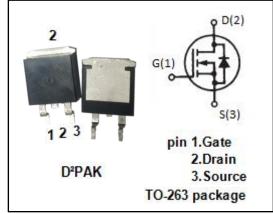
 motor drive, DC-DC converter, power switch and solenoid drive.

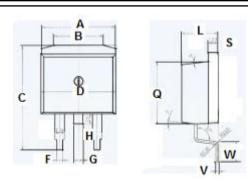
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	800	V
V <sub>GS</sub>	Gate-Source Voltage	±30	V
I <sub>D</sub>	Drain Current-continuous@ TC=25℃	10.5	А
I <sub>DM</sub>	Drain Current-Single Pulsed	42	А
P <sub>tot</sub>	Total Dissipation@TC=25℃	190	W
T <sub>j</sub>	Max. Operating Junction Temperature	-55~150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	0.66	°C/W





DIM	m	m
DIIVI	MIN	MAX
Α	9.8	10.2
В	6.6	6.8
C	15.1	15.3
D	9.6	10
F	0.7	0.9
G	1.26	1.3
Н	1.2	1.45
L	4.4	4.6
Q	9.2	9.3
S	1.25	1.35
V	0.4	0.6
W	2.6	2.8

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#### **ELECTRICAL CHARACTERISTICS (Tc=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	800		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}$ = $V_{GS}$ ; $I_D$ = 0.1mA	3.0	4.5	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 5.25A		0.75	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> = 0		±10	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 800V; V <sub>GS</sub> = 0		1.0	uA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 10.5A; V <sub>GS</sub> = 0		1.6	V

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